

IN THE CLAIMS:

Please cancel claims 9-18 without prejudice, and amend the claims as follows:

1-26. (Cancelled)

27. (Currently Amended) A method for cleaning a process chamber, comprising:

introducing at least one halogen-containing gas to the process chamber;

applying a plasma to the halogen-containing gas in the process chamber, wherein the plasma activates the halogen-containing gas to generate reactive species; and

~~employing~~ heating the process chamber with a rapid heating module located in the process chamber, wherein the rapid heating module comprises a high power lamp assembly placed at the bottom of the process chamber and a resistive heater assembly, an inductive heater assembly, or a combination thereof embedded in the chamber wall, wherein the rapid heating module increases the temperature of chamber parts and improves the surface temperature uniformity of chamber parts when the module is turned on, thereby assisting the cleaning activity of the reactive species such that the process chamber is cleaned.

28. (Original) The method of claim 27, wherein the reactive species are generated from a fluorine-containing gas or a chlorine-containing gas.

29. (Previously Presented) The method of claim 28, wherein the fluorine-containing gas is selected from the group consisting of HF, F₂, NF₃, SF₆, C₂F₆, CF₄, and C₃F₈.

30. (Currently Amended) The method of claim 27, wherein the process chamber further ~~comprising~~ comprises liners disposed in the process chamber adjacent the chamber walls.

31. (Previously Presented) The method of claim 30, wherein the resistive heater assembly is embedded in the chamber wall next to the liners.

32. (Previously Presented) The method of claim 30, wherein the inductive heater assembly is embedded in the chamber wall next to the liners.

33. (Original) The method of claim 27, wherein the process chamber is a chemical vapor deposition chamber or an etch chamber.

34. (Currently Amended) A method for cleaning a process chamber, comprising:

introducing at least one fluorine-containing gas to the process chamber;
applying a plasma to the fluorine-containing gas in the process chamber, wherein the plasma activates the fluorine-containing gas to generate reactive species; and
employing heating the process chamber with a rapid heating module located in the process chamber, wherein the rapid heating module comprises a high power lamp assembly placed at the bottom of the process chamber and a resistive heater assembly, an inductive heater assembly, or a combination thereof embedded in the chamber wall adjacent liners, wherein the rapid heating module increases the temperature of chamber parts and improves the surface temperature uniformity of chamber parts when the module is turned on, thereby assisting the cleaning activity of the reactive species such that the process chamber is cleaned.

35. (Previously Presented) The method of claim 34, wherein the fluorine-containing precursor gas is selected from the group consisting of HF, F₂, NF₃, SF₆, C₂F₆, CF₄, and C₃F₈.

36. (Original) The method of claim 34, wherein the process chamber is a chemical vapor deposition chamber or an etch chamber.

37-44 (Cancelled)

45. (Currently Amended) A method for cleaning a process chamber, comprising:

introducing at least one halogen-containing gas to a remote chamber, wherein the remote chamber is connected to the interior of the process chamber;

applying a plasma to the halogen-containing gas in the remote chamber wherein the plasma activates the halogen-containing gas to generate reactive species;

introducing the reactive species to the process chamber; and

employing heating the process chamber with a rapid heating module located in the process chamber, wherein the rapid heating module comprises a high power lamp assembly placed at the bottom of the process chamber and a resistive heater assembly, an inductive heater assembly, or a combination thereof embedded in the chamber wall, wherein the rapid heating module increases the temperature of chamber parts and improves the surface temperature uniformity of chamber parts when the module is turned on, thereby assisting the cleaning activity of the reactive species such that the process chamber is cleaned.

46. (Original) The method of claim 45, wherein the reactive species is generated from a fluorine-containing gas or a chlorine-containing gas.

47. (Previously Presented) The method of claim 46, wherein the fluorine-containing gas is selected from the group consisting of HF, F₂, NF₃, SF₆, C₂F₆, CF₄, and C₃F₈.

48. (Currently Amended) The method of claim 45, wherein the process chamber further ~~comprising~~ comprises liners disposed in the process chamber adjacent the chamber walls.

49. (Previously Presented) The method of claim 48, wherein the resistive heater assembly is embedded in the chamber wall next to the liners.

50. (Previously Presented) The method of claim 48, wherein the inductive heater assembly is embedded in the chamber wall next to the liners.

51. (Original) The method of claim 45, wherein the process chamber is a chemical vapor deposition chamber or an etch chamber.

52. (Currently Amended) A method for cleaning a process chamber, comprising:

introducing at least one fluorine-containing gas to a remote chamber, wherein the remote chamber is connected to the interior of the process chamber;

applying a plasma to the fluorine-containing gas in the remote chamber wherein the plasma activates the fluorine-containing gas to generate reactive species;

introducing the reactive species to the process chamber; and

~~employing~~ heating the process chamber with a rapid heating module located in the process chamber, wherein the rapid heating module comprises a high power lamp assembly placed at the bottom of the process chamber and a resistive heater assembly, an inductive heater assembly, or a combination thereof embedded in the chamber wall adjacent liners, wherein the rapid heating module increases the temperature of chamber parts and improves the surface temperature uniformity of chamber parts when the module is turned on, thereby assisting the cleaning activity of the reactive species such that the process chamber is cleaned.

53. (Previously Presented) The method of claim 52, wherein the fluorine-containing gas is selected from the group consisting of HF, F₂, NF₃, SF₆, C₂F₆, CF₄, and C₃F₈.

54. (Original) The method of claim 52, wherein the process chamber is a chemical vapor deposition chamber or an etch chamber.